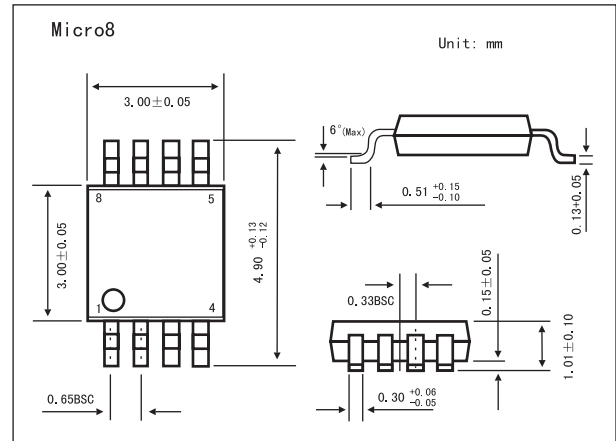
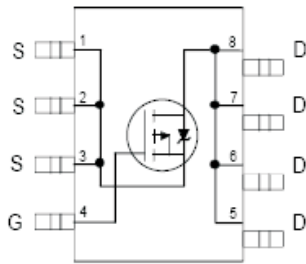


HEXFET[®] Power MOSFET

KRF7663

■ Features

- Trench Technology
- Ultra Low On-Resistance
- P-Channel MOSFET
- Very Small SOIC Package
- Low Profile (<1.1mm)
- Available in Tape & Reel



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	V
Continuous Drain Current, $V_{GS} @ -4.5V @ T_a = 25^\circ\text{C}$	I_D	-8.2	A
Continuous Drain Current, $V_{GS} @ -4.5V @ T_a = 70^\circ\text{C}$	I_D	-6.6	
Pulsed Drain Current *1	I_{DM}	-66	
Power Dissipation @ $T_a = 25^\circ\text{C}$	P_D	1.8	W
Power Dissipation @ $T_a = 70^\circ\text{C}$		1.15	
Linear Derating Factor		10	mW/ $^\circ\text{C}$
Single Pulse Avalanche Energy *2	E_{AS}	115	mJ
Gate-to-Source Voltage	V_{GS}	± 12	V
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to + 150	$^\circ\text{C}$
Maximum Junction-to-Ambient *3	$R_{\theta JA}$	70	$^\circ\text{C/W}$

*1 Repetitive rating; pulse width limited by max. junction temperature.

*2 Starting $T_J = 25^\circ\text{C}$, $L = 17.8\text{mH}$, $R_G = 25\Omega$, $I_{AS} = -3.6\text{A}$

*3 When mounted on 1 inch square copper board, $t < 10\text{ sec}$

KRF7663

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250 \mu A$	-20			V
Breakdown Voltage Temp. Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = -1mA, \text{Reference to } 25^\circ C$		-0.01		V/°C
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -7.0A^{*1}$			0.02	Ω
		$V_{GS} = -2.5V, I_D = -5.1A^{*1}$			0.04	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.60		-1.2	V
Forward Transconductance	g_{fs}	$V_{DS} = -10V, I_D = -7.0A^{*1}$	14.5			S
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS} = -16V, V_{GS} = 0V$			-1.0	μA
		$V_{DS} = -16V, V_{GS} = 0V, T_J = 70^\circ C$			-25	
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS} = -12V$			-100	nA
Gate-to-Source Reverse Leakage		$V_{GS} = 12V$			100	
Total Gate Charge	Q_g	$I_D = -6.0A$		30	45	nC
Gate-to-Source Charge	Q_{gs}	$V_{DS} = -10V$		5.0	7.5	
Gate-to-Drain ("Miller") Charge	Q_{gd}	$V_{GS} = -5V$		7.0	10.5	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10V$		11		ns
Rise Time	t_r	$I_D = -6A$		100		
Turn-Off Delay Time	$t_{d(off)}$	$R_G = 6.2 \Omega$		125		
Fall Time	t_f	$R_D = 1.64 \Omega$		172		
Input Capacitance	C_{iss}	$V_{GS} = 0V$		2520		pF
Output Capacitance	C_{oss}	$V_{DS} = -10V$		615		
Reverse Transfer Capacitance	C_{rss}	$f = 1.0MHz$		375		
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode. 			-1.8	A
Pulsed Source Current (Body Diode) *2	I_{SM}				-66	
Diode Forward Voltage	V_{SD}	$T_J = 25^\circ C, I_S = -7A, V_{GS} = 0V^{*1}$			-1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ C, I_F = -2.5A$		70	105	ns
Reverse Recovery Charge	Q_{rr}	$di/dt = -100A/\mu s^{*1}$		50	75	μC

*1 Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.

*2 Repetitive rating; pulse width limited by max. junction temperature.